

MA2J704

Silicon epitaxial planar type

For super-high speed switching circuit

■ Features

- S-mini type 2-pin package
- Allowing to rectify under ($I_{F(AV)} = 200$ mA) condition
- Low I_R (reverse current) type. (About 1/10 of I_R of the ordinary products)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

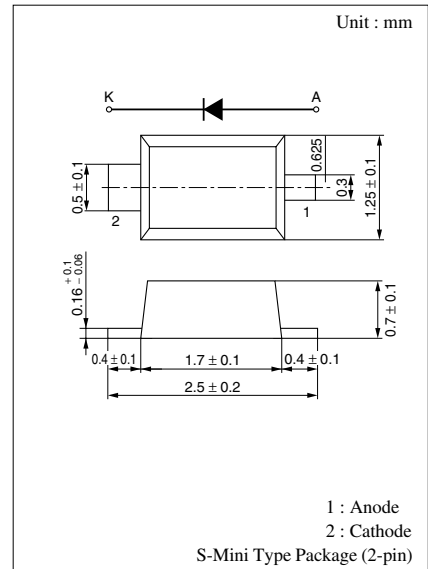
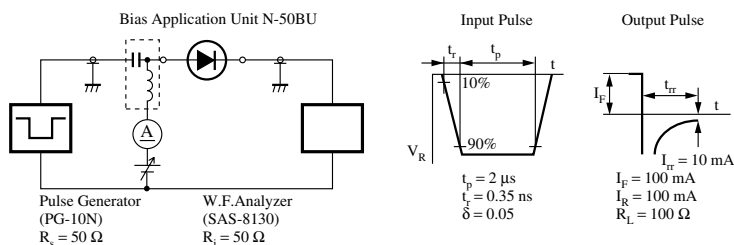
Note) *: The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_{R1}	$V_R = 10$ V			2	μA
	I_{R2}	$V_R = 20$ V			5	μA
Forward voltage (DC)	V_F	$I_F = 200$ mA			0.55	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		30		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 0.1 \cdot I_R$, $R_L = 100 \Omega$		3.0		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 1 000 MHz
3. *: t_{rr} measuring circuit



Marking Symbol: 2S

Internal Connection

